

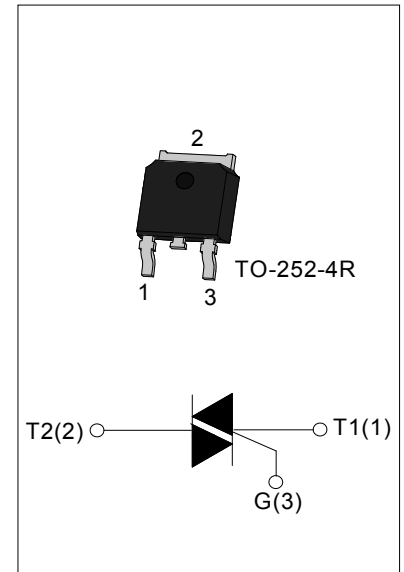


DESCRIPTION:

With high ability to withstand the shock loading of large current, JST04 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. Package TO-252-4R is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
V_{DRM}/V_{RRM}	600/800	V
$I_{T(RMS)}$	4	A



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)		V_{RRM}	600/800	V
RMS on-state current	TO-252-4R ($T_c=100^{\circ}C$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	40	A
I^2t value for fusing ($t_p=10ms$)		I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	50	$A/\mu s$
Peak gate current		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	10	35	50	mA
V_{GT}		I - II -III	MAX	1.5				V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	10	20	50	70	mA
		II		15	35	60	80	
I_H	$I_T=100\text{mA}$		MAX	10	15	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	50	100	400	1000	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5.5\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	10	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.75	mA

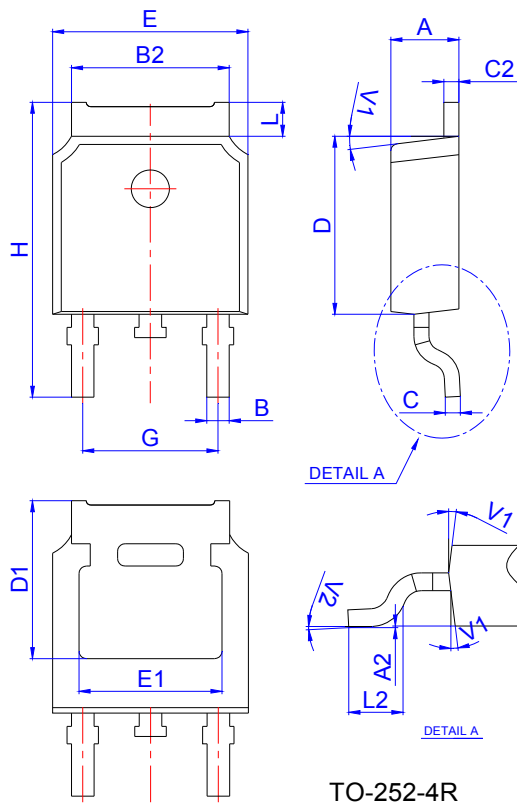
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252-4R	2.8	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient		70	

ORDERING INFORMATION

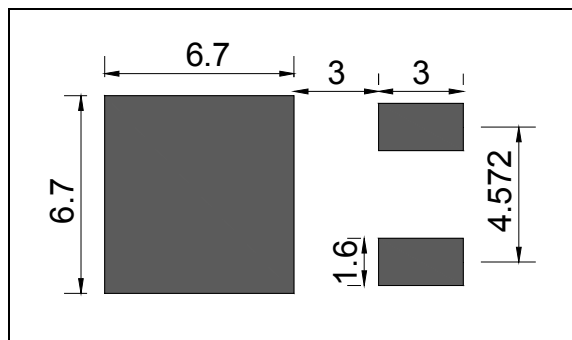
<p>J</p> <p>JieJie Microelectronics Co.,Ltd</p>	<p>ST</p> <p>Triacs</p> <p>$I_{T(RMS)}:4\text{A}$</p> <p>K:TO-252-4R KTR:TO-252-4R(Tape&Reel)</p>	<p>04</p>	<p>K</p>	<p>-600</p> <p>600:$V_{DRM} V_{RRM}\geq 600\text{V}$ 800:$V_{DRM} V_{RRM}\geq 800\text{V}$</p>	<p>TW</p> <p>TW: $I_{GT1-3}\leq 5\text{mA}$ SW: $I_{GT1-3}\leq 10\text{mA}$ CW: $I_{GT1-3}\leq 35\text{mA}$ BW: $I_{GT1-3}\leq 50\text{mA}$</p>
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PACKAGE MECHANICAL DATA

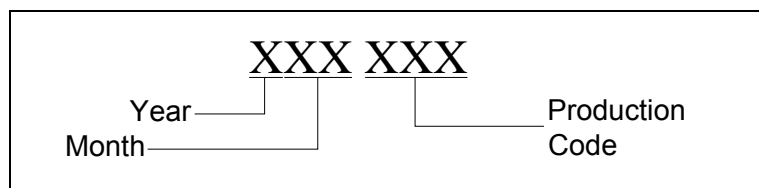
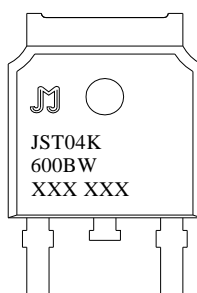


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

FOOTPRINT-TO-252-4R (dimensions in mm)



MARKING



PACKAGE INFORMATION

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TAPING	2,500	25,000	13 inch

FIG.1: Maximum power dissipation versus RMS on-state current

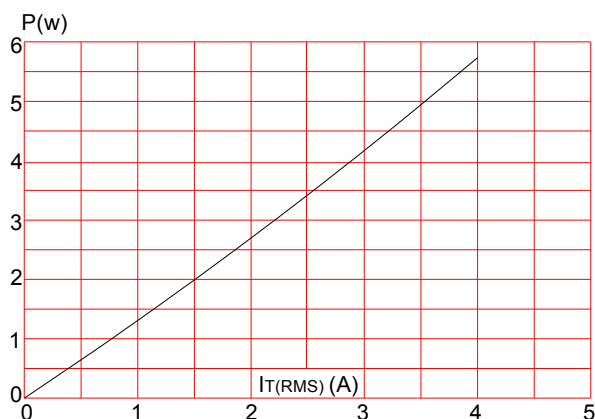


FIG.3: Surge peak on-state current versus number of cycles

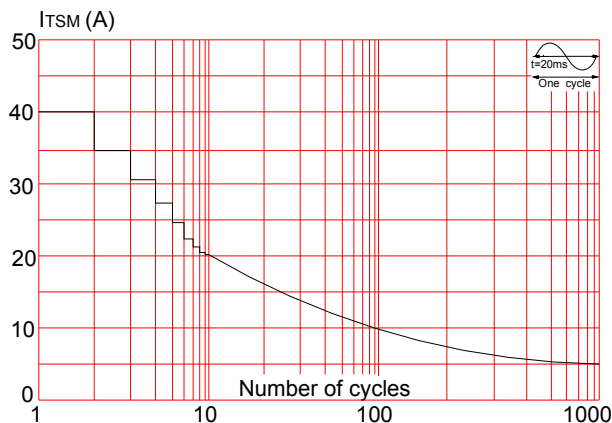


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35μm)(full cycle)

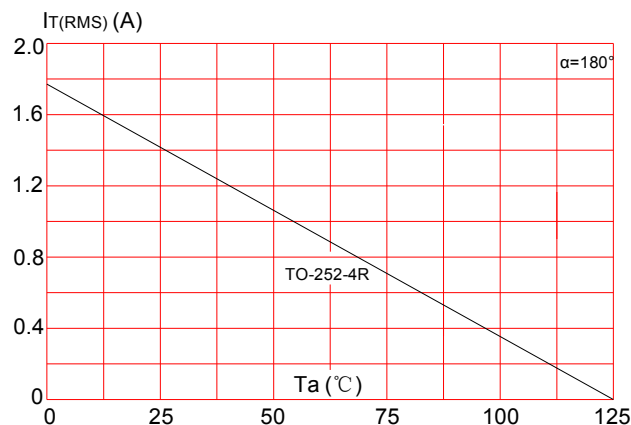


FIG.4: On-state characteristics (maximum values)

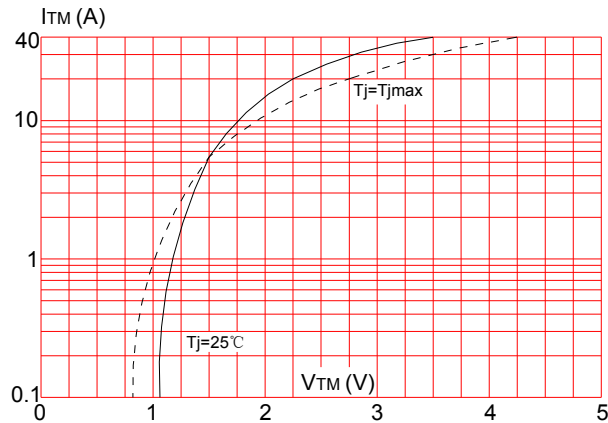


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

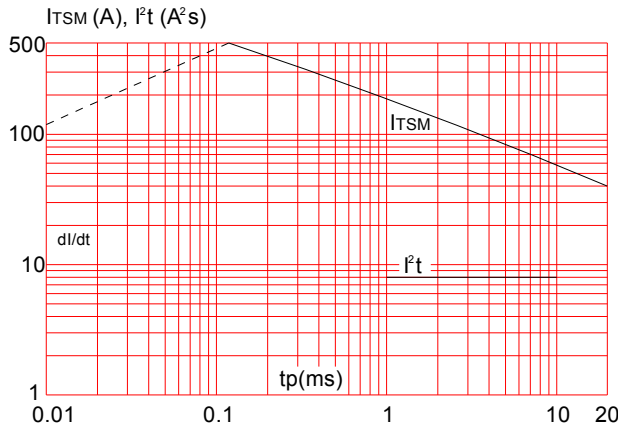
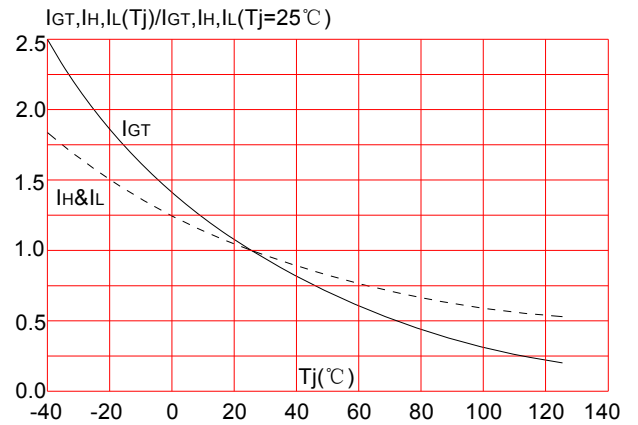
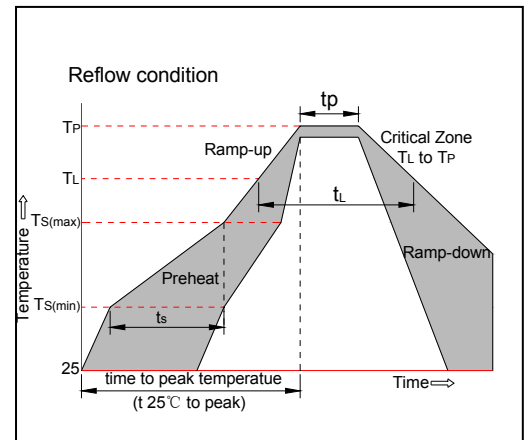


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max ($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (T_L) (Liquidus)	+217°C
	-Temperature (t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C




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